HALOGEN

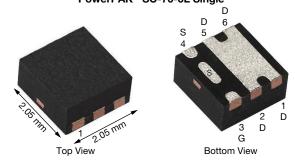
FREE

Vishay Siliconix

P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}$ (Ω) (Max.)	I _D (A) ^a	Q _g (Typ.)						
	0.0145 at V _{GS} = -4.5 V	-29.7							
-20	0.0205 at V _{GS} = -2.5 V	-25	28 nC						
-20	0.0330 at V _{GS} = -1.8 V	-19.7							
	0.0650 at $V_{GS} = -1.5 \text{ V}$	-4							

PowerPAK® SC-70-6L Single



Marking Code: BU **Ordering Information:**

SiA437DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-70 package RoHS



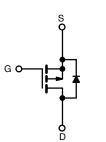
- Low On-Resistance

100 % R_a tested

· Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Providing low voltage drop in smart phones, tablet PCs, mobile computing:
- Battery switches
- Load switches
- Power management



P-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-20		
Gate-Source Voltage		V _{GS}	± 8	V	
	T _C = 25 °C		-29.7		
Continuous Dunis Comment /T. 150 °C	T _C = 70 °C		-23.8		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	-12.6 ^{b, c}		
	T _A = 70 °C		-10 ^{b, c}	А	
Pulsed Drain Current (t = 300 μs)		I _{DM}	-60		
0 " 0 5 5 1 0 1	T _C = 25 °C	,	-16		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	-2.9 b, c		
	T _C = 25 °C		19		
Martin or Brown Black after	T _C = 70 °C	5	12	,,,	
Maximum Power Dissipation	T _A = 25 °C	P _D	3.5 ^{b, c}	W	
	T _A = 70 °C		2.2 b, c		
Operating Junction and Storage Temperature R	ange	T _J , T _{stg}	-50 to 150	°C	
Soldering Recommendations (Peak Temperatur	e) ^{d, e}	_	260		

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient b, f	t ≤ 5 s	R_{thJA}	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	5.3	6.5	0/00				

Notes

- a. $T_C = 25$ °C.
- b. Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 80 °C/W.

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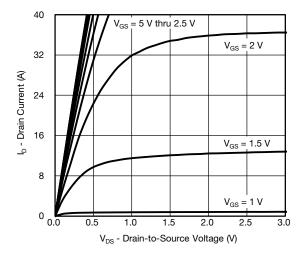
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static				l		L			
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20	-	-	V			
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$		-	-11	-	mV/°C			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μA	-	2.5	-				
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.4	-	-0.9	V			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	-	± 100	nA			
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	μΑ			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10	-	-	Α			
	, ,	V _{GS} = -4.5 V, I _D = -8 A	-	0.0120	0.0145	Ω			
	_	V _{GS} = -2.5 V, I _D = -5 A	-	0.0170	0.0205				
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = -1.8 V, I _D = -2 A	-	0.0250	0.0330				
		V _{GS} = -1.5 V, I _D = -2 A	-	0.0370	0.0650	=			
Forward Transconductance a	9 _{fs}	V _{GS} = -10 V, I _D = -8 A	-	32	-	S			
Dynamic ^b				l		l			
Input Capacitance	C _{iss}			2340	-				
Output Capacitance	C _{oss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	-	305	-	pF			
Reverse Transfer Capacitance	C _{rss}		-	270	-				
		V _{DS} = -10 V, V _{GS} = -8 V, I _D = -13 A	-	60	90	nC			
Total Gate Charge	Q _g		-	28	43				
Gate-Source Charge		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -13 \text{ A}$	-	4.2	-				
Gate-Drain Charge	Q_{qd}		-	6.8	-				
Gate Resistance	R_g	f = 1 MHz	1.6	8	16	Ω			
Turn-On Delay Time	t _{d(on)}		-	20	40	- ns			
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{I} = 1 \Omega$	-	22	45				
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -10 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	-	100	200				
Fall Time	t _f		-	37	75				
Turn-On Delay Time	t _{d(on)}		-	10	20				
Rise Time	t_r $V_{DD} = -10 \text{ V. Ri} = 1 \Omega$		-	10	20	1			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -10 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$	-	120	240				
Fall Time	t _f		-	34	70				
Drain-Source Body Diode Characterist	cs								
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	-16	_			
Pulse Diode Forward Current	Diode Forward Current I _{SM}		-	-	-60	Α			
Body Diode Voltage	V _{SD}	I _S = -10 A, V _{GS} = 0 V	-	-0.75	-1.2	V			
Body Diode Reverse Recovery Time	t _{rr}		-	12	25	ns			
Body Diode Reverse Recovery Charge	Q _{rr}	10001/44 1000/ 7 0500	-	4	10	nC			
Reverse Recovery Fall Time	ta	$I_F = -10 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$	-	7.5	-	ns			
Reverse Recovery Rise Time	t _b		-	4.5	_				

Notes

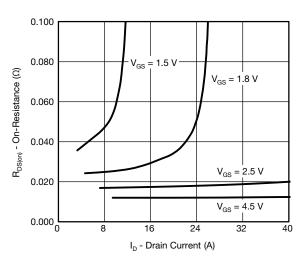
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

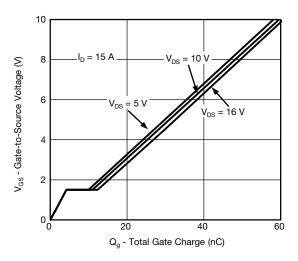




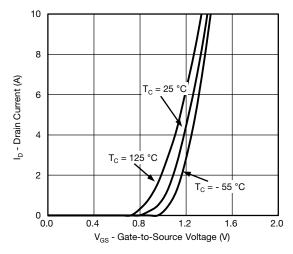
Output Characteristics



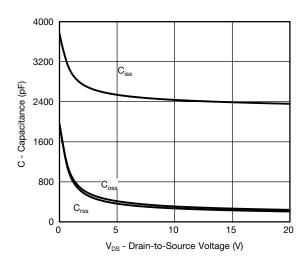
On-Resistance vs. Drain Current and Gate Voltage



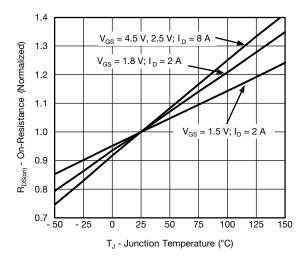
Gate Charge



Transfer Characteristics

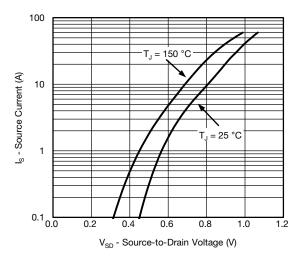


Capacitance

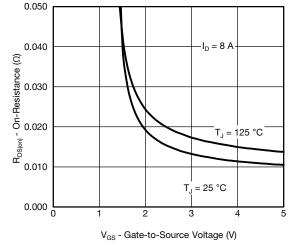


On-Resistance vs. Junction Temperature

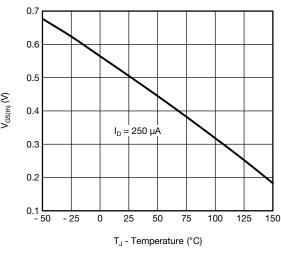




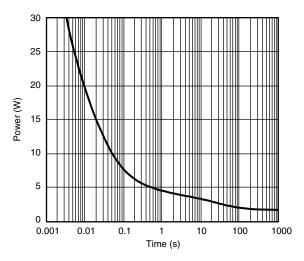
Source-Drain Diode Forward Voltage



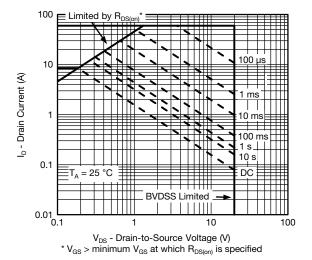
On-Resistance vs. Gate-to-Source Voltage



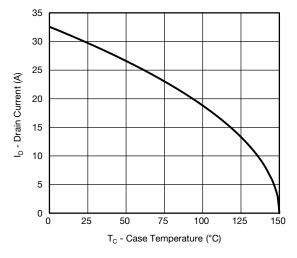
Threshold Voltage

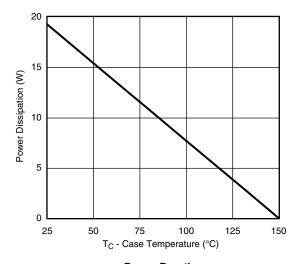


Single Pulse Power, Junction-to-Ambient







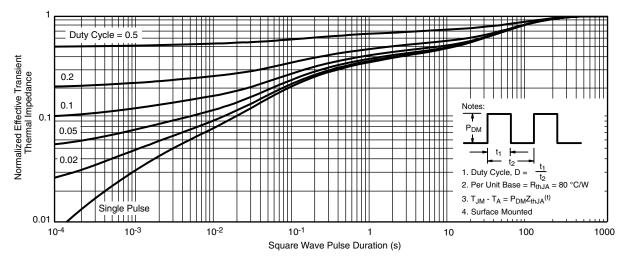


Current Derating*

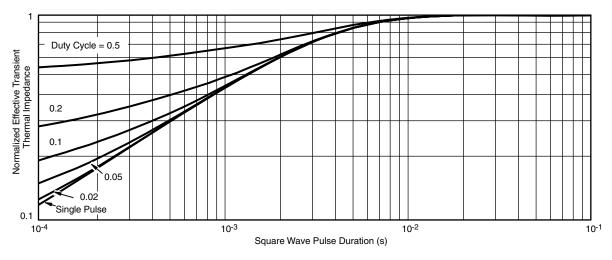
Power Derating

^{*} The power dissipation P_D is based on $T_{J \text{ (max.)}} = 150 \,^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

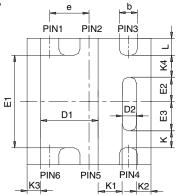
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62777.





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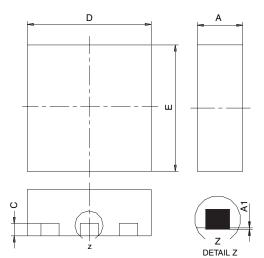
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

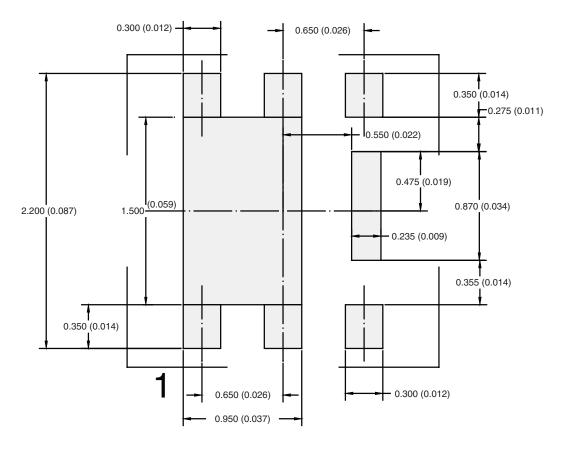
	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP	1		0.011 TYP		0.275 TYP			0.011 TYP		
K1		0.400 TYP	1	0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP 0.009 TYP			0.252 TYP 0.010 TYP				1			
К3		0.225 TYP	1	0.009 TYP								
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
FCN: C-07431 - Bey. C. 06-Aug-07												

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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